

POWER MOS V® FREDFET

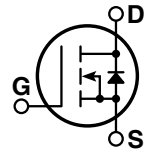
Power MOS V® is a new generation of high voltage N-Channel enhancement mode power MOSFETs. This new technology minimizes the JFET effect, increases packing density and reduces the on-resistance. Power MOS V® also achieves faster switching speeds through optimized gate layout.



- **Faster Switching**
- **Lower Leakage**
- **Popular SOT-227 Package**

- **Avalanche Energy Rated**

• **FAST RECOVERY BODY DIODE**


MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT60M75JVFR	UNIT
V_{DSS}	Drain-Source Voltage	600	Volts
I_D	Continuous Drain Current @ $T_C = 25^\circ\text{C}$	62	Amps
I_{DM}	Pulsed Drain Current ^①	248	
V_{GS}	Gate-Source Voltage Continuous	± 30	Volts
V_{GSM}	Gate-Source Voltage Transient	± 40	
P_D	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	700	Watts
	Linear Derating Factor	5.6	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
T_L	Lead Temperature: 0.063" from Case for 10 Sec.	300	
I_{AR}	Avalanche Current ^① (Repetitive and Non-Repetitive)	62	Amps
E_{AR}	Repetitive Avalanche Energy ^①	50	mJ
E_{AS}	Single Pulse Avalanche Energy ^④	3600	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage ($V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$)	600			Volts
$I_{D(on)}$	On State Drain Current ^② ($V_{DS} > I_{D(on)} \times R_{DS(on)}$ Max, $V_{GS} = 10\text{V}$)	62			Amps
$R_{DS(on)}$	Drain-Source On-State Resistance ^② ($V_{GS} = 10\text{V}, I_D = 31\text{A}$)			0.075	Ohms
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = 600\text{V}, V_{GS} = 0\text{V}$)			250	μA
	Zero Gate Voltage Drain Current ($V_{DS} = 480\text{V}, V_{GS} = 0\text{V}, T_C = 125^\circ\text{C}$)			1000	
I_{GSS}	Gate-Source Leakage Current ($V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$)			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 5\text{mA}$)	2		4	Volts

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

DYNAMIC CHARACTERISTICS

APT60M75JVFR

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C _{iss}	Input Capacitance	V _{GS} = 0V		16500	19800	pF
C _{oss}	Output Capacitance	V _{DS} = 25V		1900	2660	
C _{rss}	Reverse Transfer Capacitance	f = 1 MHz		750	1125	
Q _g	Total Gate Charge ③	V _{GS} = 10V		700	1050	nC
Q _{gs}	Gate-Source Charge	V _{DD} = 300V		80	120	
Q _{gd}	Gate-Drain ("Miller") Charge	I _D = 62A @ 25°C		330	495	
t _{d(on)}	Turn-on Delay Time	V _{GS} = 15V		20	40	ns
t _r	Rise Time	V _{DD} = 300V		20	40	
t _{d(off)}	Turn-off Delay Time	I _D = 62A @ 25°C		80	120	
t _f	Fall Time	R _G = 0.6Ω		12	24	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
I _S	Continuous Source Current (Body Diode)			62	Amps
I _{SM}	Pulsed Source Current ① (Body Diode)			248	
V _{SD}	Diode Forward Voltage ② (V _{GS} = 0V, I _S = - 62A)			1.3	Volts
dv/dt	Peak Diode Recovery dv/dt ⑤			15	V/ns
t _{rr}	Reverse Recovery Time (I _S = -62A, di/dt = 100A/μs)	T _J = 25°C		300	ns
		T _J = 125°C		600	
Q _{rr}	Reverse Recovery Charge (I _S = -62A, di/dt = 100A/μs)	T _J = 25°C		1.8	μC
		T _J = 125°C		7.4	
I _{RRM}	Peak Recovery Current (I _S = -62A, di/dt = 100A/μs)	T _J = 25°C		16	Amps
		T _J = 125°C		30	

THERMAL/PACKAGE CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
R _{θJC}	Junction to Case			0.18	°C/W
R _{θJA}	Junction to Ambient			40	
V _{Isolation}	RMS Voltage (50-60 Hz Sinusoidal Waveform From Terminals to Mounting Base for 1 Min.)	2500			Volts
Torque	Maximum Torque for Device Mounting Screws and Electrical Terminations			10	lb•in

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② Pulse Test: Pulse width < 380 μs, Duty Cycle < 2%

③ See MIL-STD-750 Method 3471

④ Starting T_J = +25°C, L = 1.87mH, R_G = 25Ω, Peak I_L = 62A

⑤ I_S ≤ I_D = 62A, di/dt = 100A/μs, T_J ≤ 150°C, R_G = 2.0Ω V_R = 600V.

APT Reserves the right to change, without notice, the specifications and information contained herein.

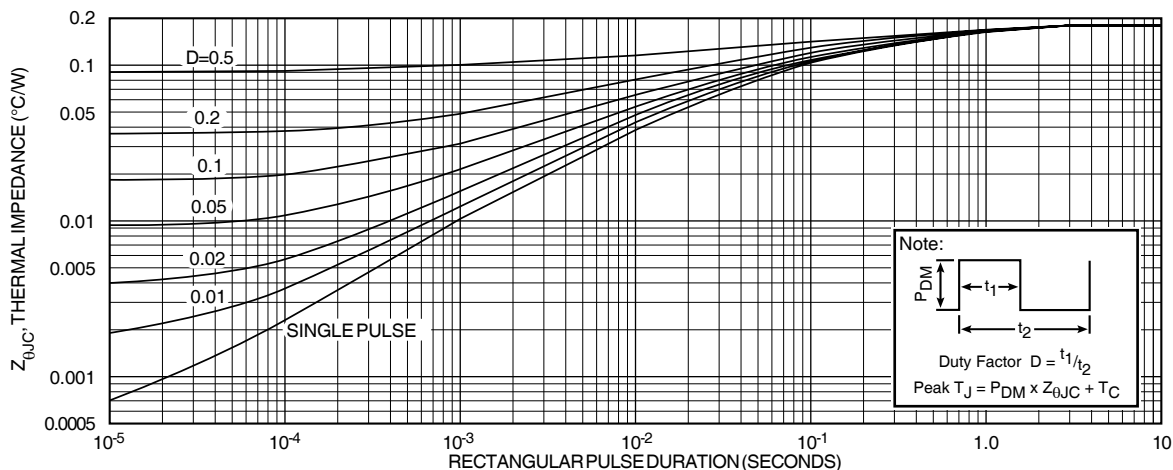


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

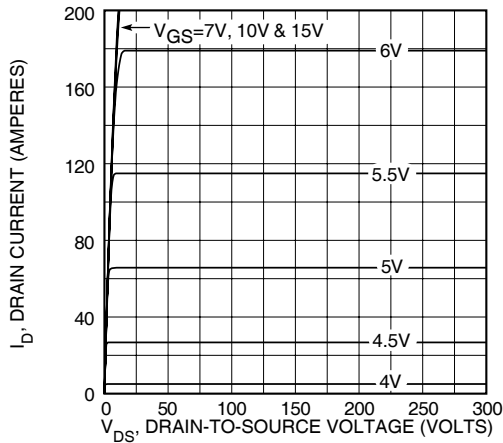


FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS

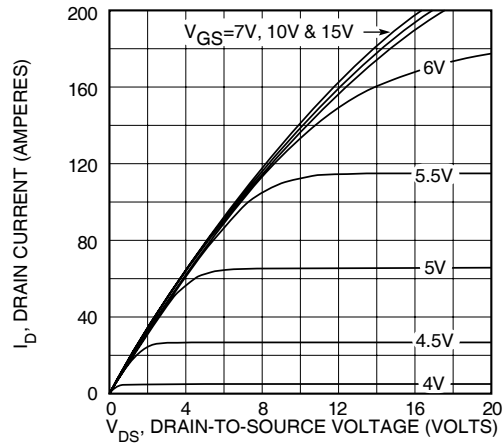


FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS

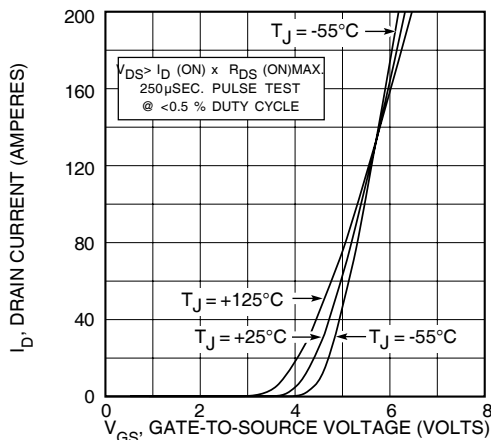


FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS

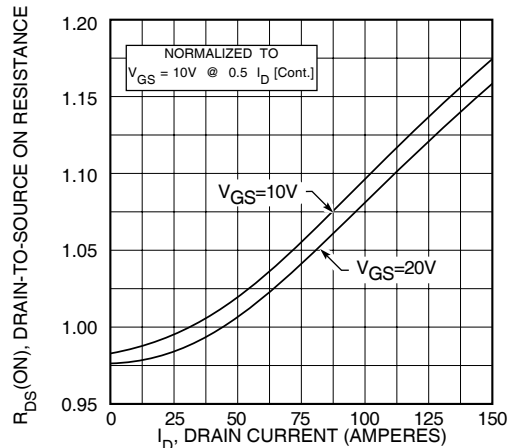


FIGURE 5, $R_{DS(ON)}$ vs DRAIN CURRENT

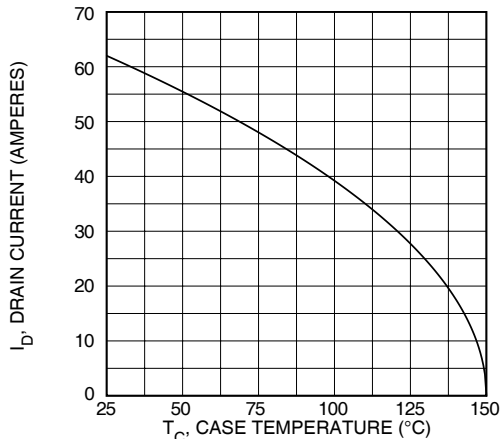


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

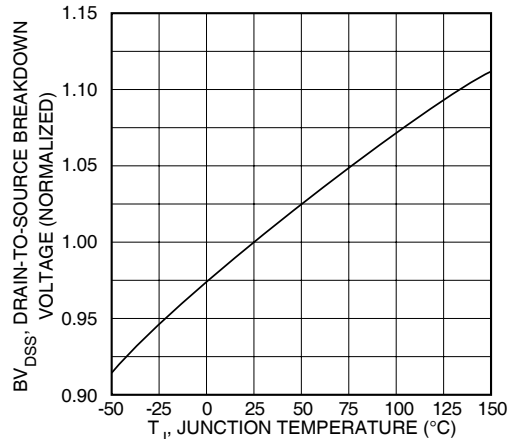


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

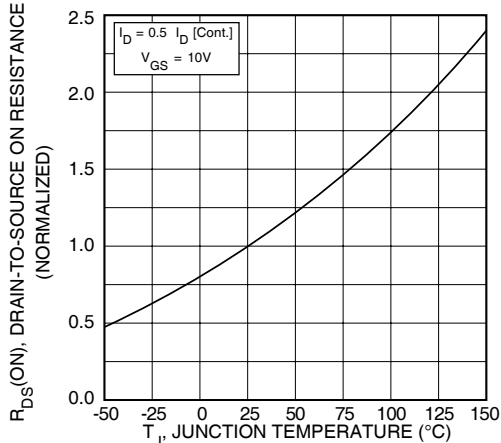


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

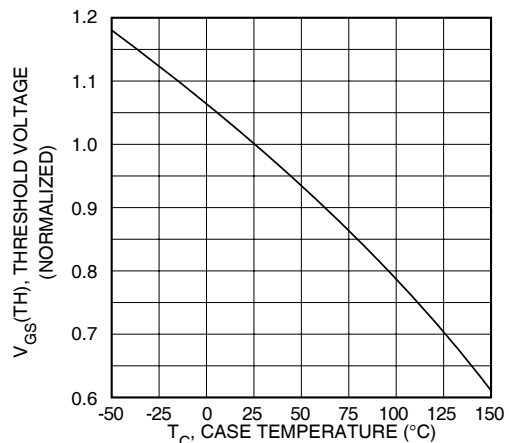


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

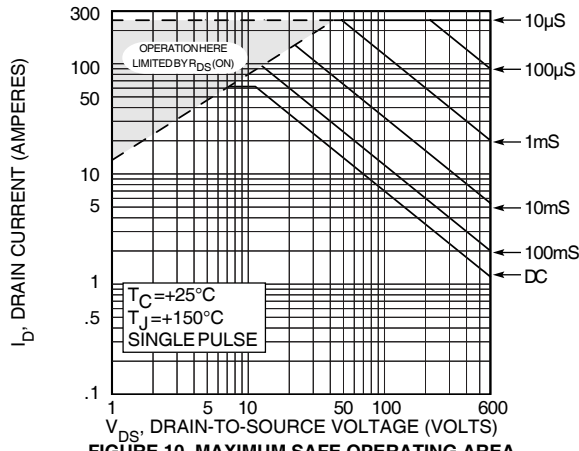


FIGURE 10, MAXIMUM SAFE OPERATING AREA

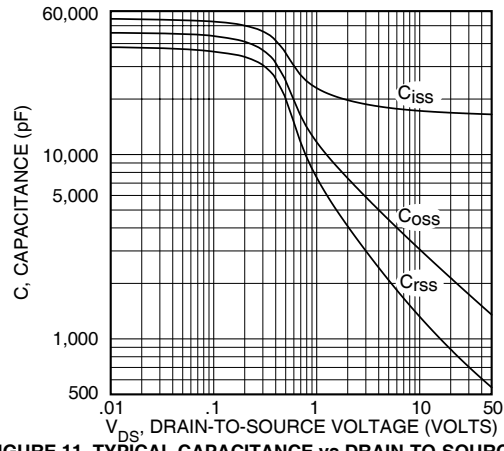


FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

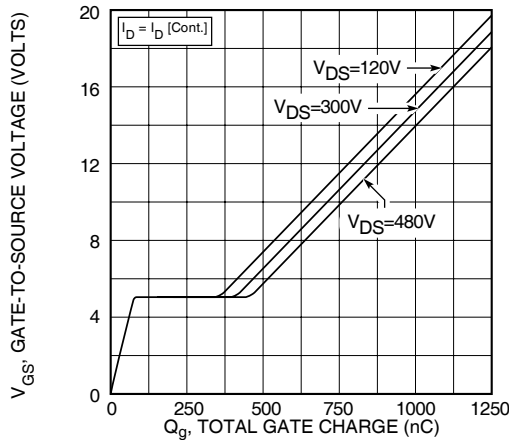


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

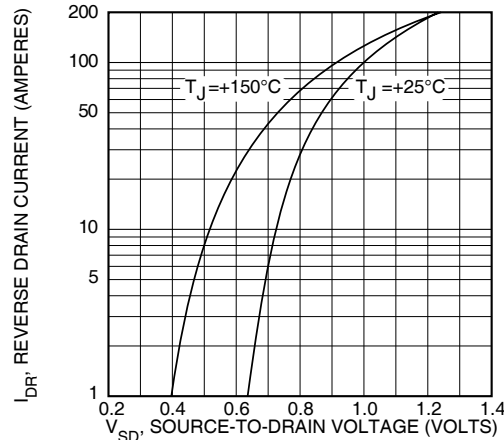
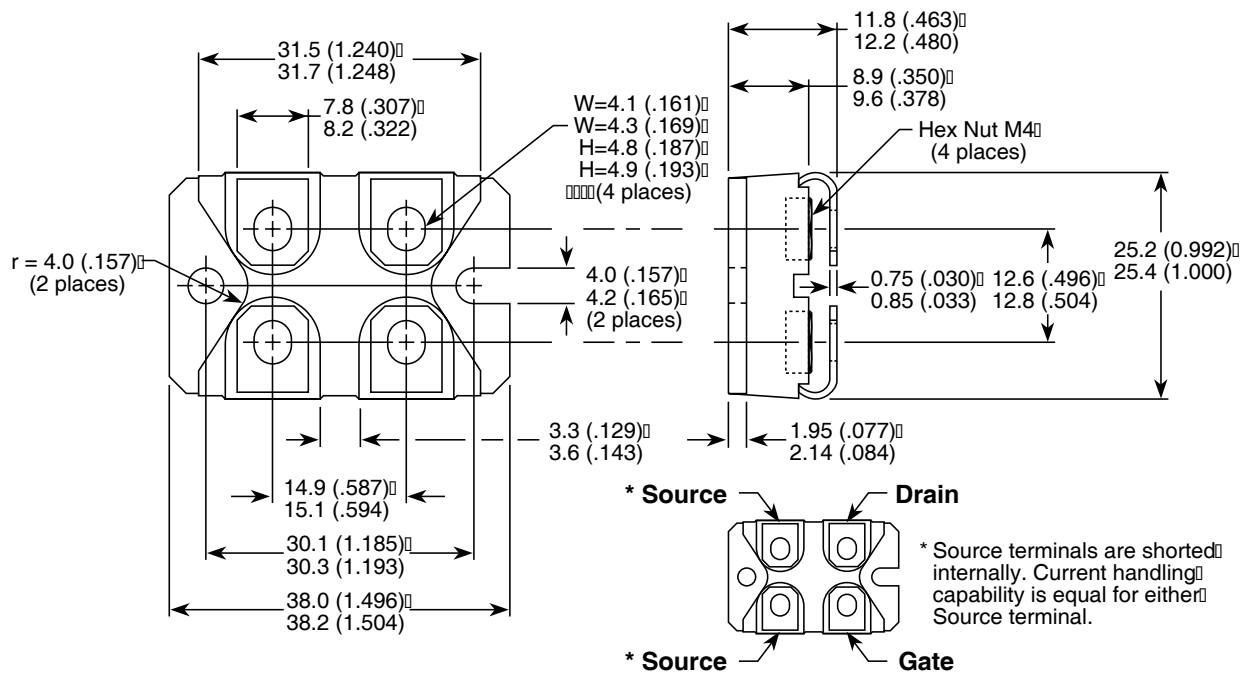


FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE

SOT-227 (ISOTOP®) Package Outline



Dimensions in Millimeters and (Inches)

ISOTOP® is a Registered Trademark of SGS Thomson.

UL Recognized File No. E145592

APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522

5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. US and Foreign patents pending. All Rights Reserved.